

MOSFET Maximum Ratings T_J = 25°C unless otherwise noted

Symbol	Parameter		Ratings	Units	
V _{DSS}	Drain-to-Source Voltage		40	V	
V _{GS}	Gate-to-Source Voltage		±20	V	
I _D	Drain Current - Continuous (V _{GS} =10) (Note 1)	T _C =25°C	110	٨	
	Pulsed Drain Current	T _C = 25°C	See Figure 4	— A	
E _{AS}	Single Pulse Avalanche Energy	(Note 2)	174	mJ	
-	Power Dissipation		176	W	
P _D	Derate above 25°C		1.18	W/ ^o C	
T _J , T _{STG}	Operating and Storage Temperature		-55 to + 175	°C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case		0.85	°C/W	
$R_{\theta JA}$	Maximum Thermal Resistance, Junction to Ambient	(Note 3)	43	°C/W	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDI9406	FDI9406_F085	TO-262AB	Tube	N/A	50 units

Notes:

1: Current is limited by bondwire configuration.

2: Starting T_J = 25°C, L = 0.045mH, I_{AS} = 88A, V_{DD} = 40V during inductor charging and V_{DD} = 0V during time in avalanche. 3: $R_{\theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder ⁴⁰⁰ mounting surface of the drain pins. $R_{\theta JC}$ is guaranteed by design while $R_{\theta JA}$ is determined by the user's board design. The maximum rating presented here is based on mounting on a 1 in² pad of 2oz copper.

Symbol	Parameter	Test Conditions		Min.	Тур.	Max.	Units
Off Cha	racteristics						
B _{VDSS}	Drain-to-Source Breakdown Voltage	I _D = 250μA, V _G	_S = 0V	40	-	-	V
	Drain-to-Source Leakage Current	V _{DS} =40V,	T _J = 25 ^o C	-	-	1	μA
DSS		V _{GS} = 0V	$T_J = 175^{\circ}C(Note 4)$	-	-	1	mA
I _{GSS}	Gate-to-Source Leakage Current	$V_{GS} = \pm 20V$		-	-	±100	nA
R _{DS(on)}	Drain-to-Source On Resistance	I _D = 80A,		-	1.73	2.2	mΩ
V _{GS(th)}	Gate-to-Source Threshold Voltage	$V_{GS} = V_{DS}, I_D =$	= 250μA	2.0	2.83	4.0	V
R _{DS(on)}	Drain-to-Source On Resistance		$T_{1} = 175^{\circ}C(Note 4)$	-	2.86	3.2	mΩ
Dynami C _{iss}	c Characteristics				7710	-	pF
C _{iss} C _{oss}	Output Capacitance	V _{DS} = 25V, V _{GS}	_S = 0V,		2015	-	pF
C _{rss}	Reverse Transfer Capacitance	f = 1MHz		_	140	-	pF
R _g	Gate Resistance			-	2.7	-	Ω
Q _{g(ToT)}	Total Gate Charge at 10V	$V_{GS} = 0$ to 10V	1/ - 321/	-	107	138	nC
Q _{g(th)}	Threshold Gate Charge	$V_{GS} = 0$ to 2V	V _{DD} = 32V I _D = 80A	-	14	19	nC
Q _{gs}	Gate-to-Source Gate Charge			-	33	-	nC
90	l l						

Switching Characteristics

Gate-to-Drain "Miller" Charge

t _{on}	Turn-On Time		-	-	160	ns
t _{d(on)}	Turn-On Delay		-	32	-	ns
t _r	Rise Time	V _{DD} = 20V, I _D = 80A,	-	81	-	ns
t _{d(off)}	Turn-Off Delay	V_{DD} = 20V, I _D = 80A, V _{GS} = 10V, R _{GEN} = 6Ω	-	50	-	ns
t _f	Fall Time		-	23	-	ns
t _{off}	Turn-Off Time		-	-	93	ns

Drain-Source Diode Characteristics

V_{SD}	Source-to-Drain Diode Voltage	I _{SD} = 80A, V _{GS} = 0V	-	-	1.25	V
t _{rr}	Reverse-Recovery Time	I _F = 80A, dI _{SD} /dt = 100A/μs,	-	85	110	ns
Q _{rr}	Reverse-Recovery Charge	V _{DD} =32V	-	122	160	nC

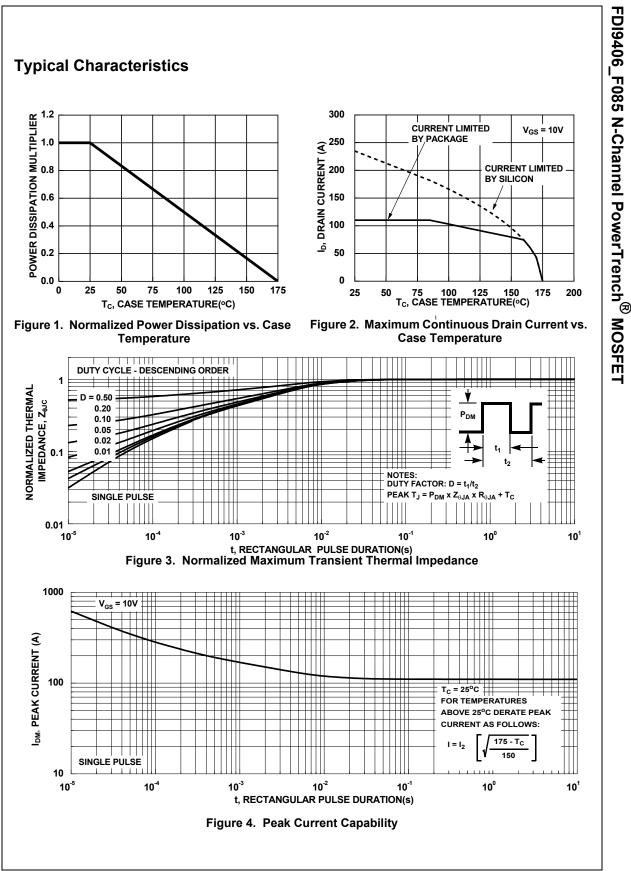
Note:

Q_{gd}

4: The maximum value is specified by design at T_J = 175°C. Product is not tested to this condition in production.

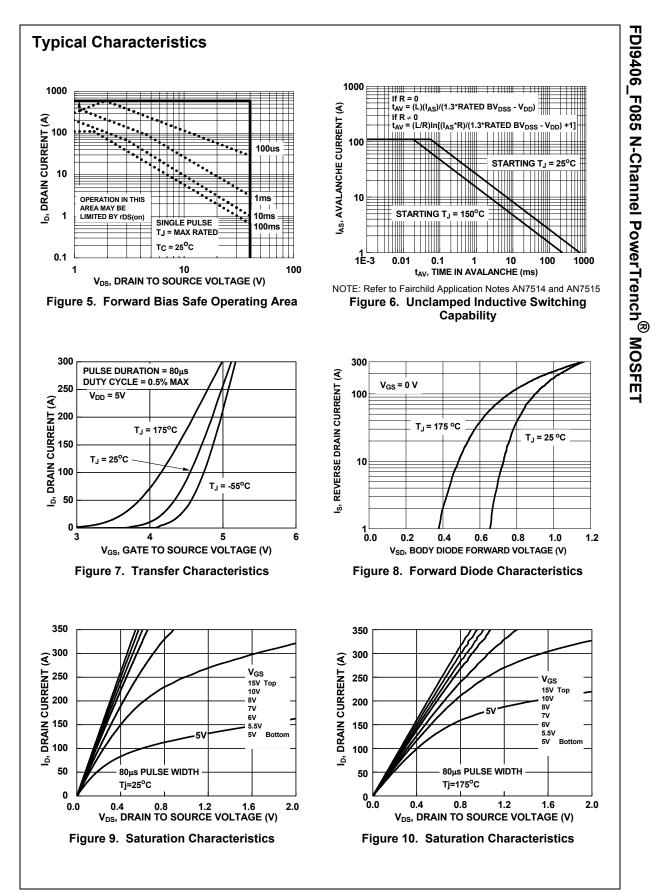
18

nC

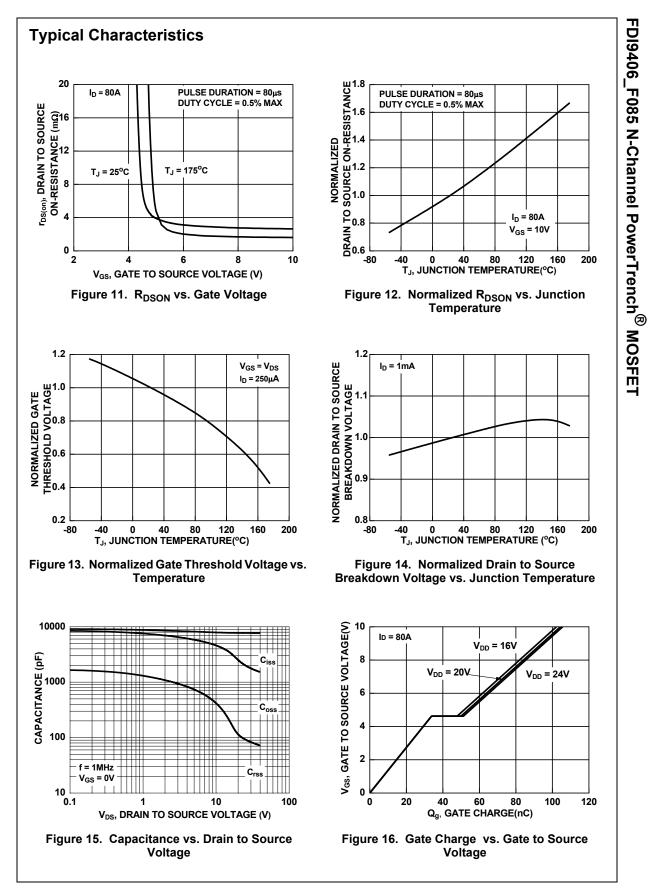


FDI9406_F085 Rev. C3

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FDI9406_F085 Rev. C3





Obsolete

Not In Production

Datasheet contains specifications on a product that is discontinued by Fairchild

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